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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	CANbus, I²C, SCI, SPI
Peripherals	LVD, PWM, WDT
Number of I/O	69
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 24x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcf51ac128aclke

1.3 Features

Table 2 describes the functional units of the MCF51AC256 series.

Table 2. MCF51AC256 Series Functional Units

Functional Unit	Function
CF1 Core (V1 ColdFire core)	Executes programs and interrupt handlers
BDM (background debug module)	Provides single pin debugging interface (part of the V1 ColdFire core)
DBG (debug)	Provides debugging and emulation capabilities (part of the V1 ColdFire core)
VBUS (debug visibility bus)	Allows for real-time program traces (part of the V1 ColdFire core)
SIM (system integration module)	Controls resets and chip level interfaces between modules
Flash (flash memory)	Provides storage for program code, constants and variables
RAM (random-access memory)	Provides storage for program variables
RGPIO (rapid general-purpose input/output)	Allows for I/O port access at CPU clock speeds
VREG (voltage regulator)	Controls power management across the device
COP (computer operating properly)	Monitors a countdown timer and generates a reset if the timer is not regularly reset by the software
LVD (low-voltage detect)	Monitors internal and external supply voltage levels, and generates a reset or interrupt when the voltages are too low
CF1_INTC (interrupt controller)	Controls and prioritizes all device interrupts
ADC (analog-to-digital converter)	Measures analog voltages at up to 12 bits of resolution
FTM1, FTM2 (flexible timer/pulse-width modulators)	Provides a variety of timing-based features
TPM3 (timer/pulse-width modulator)	Provides a variety of timing-based features
CRC (cyclic redundancy check)	Accelerates computation of CRC values for ranges of memory
ACMP1, ACMP2 (analog comparators)	Compares two analog inputs
IIC (inter-integrated circuit)	Supports standard IIC communications protocol
KBI (keyboard interrupt)	Provides pin interrupt capabilities
MCG (multipurpose clock generator)	Provides clocking options for the device, including a phase-locked loop (PLL) and frequency-locked loop (FLL) for multiplying slower reference clock sources
OSC (crystal oscillator)	Allows a crystal or ceramic resonator to be used as the system clock source or reference clock for the PLL or FLL
LPO (low-power oscillator)	Provides a second clock source for COP and RTI.
CAN (controller area network)	Supports standard CAN communications protocol
SCI1, SCI2 (serial communications interfaces)	Serial communications UARTs capable of supporting RS-232 and LIN protocols
SPI1 (8-bit serial peripheral interfaces)	Provides 8-bit 4-pin synchronous serial interface
SPI2 (16-bit serial peripheral interfaces)	Provides 16-bit 4-pin synchronous serial interface with FIFO

— Double-buffered transmit and receive
— Serial clock phase and polarity options
— Slave select output
— Selectable MSB-first or LSB-first shifting
— 16-bit and FIFO operations in SPI2

- Input/Output
  — 69 GPIOs
  — 8 keyboard interrupt pins with selectable polarity
  — Hysteresis and configurable pull-up device on all input pins; Configurable slew rate and drive strength on all output pins
  — 16-bits Rapid GPIO pins connected to the processor's local 32-bit platform bus with set, clear, and faster toggle functionality

1.4 Part Numbers

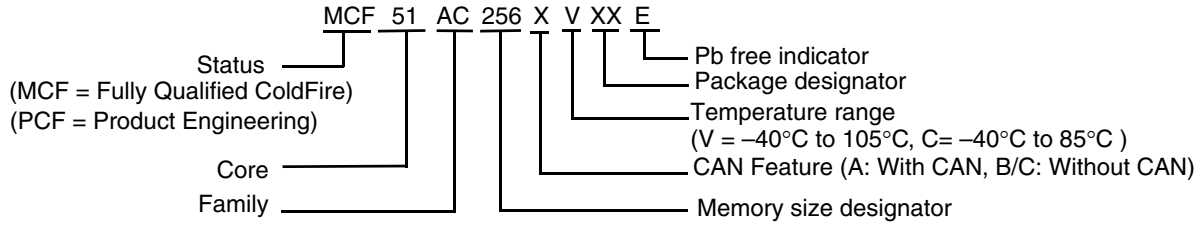


Table 3. Orderable Part Number Summary

Freescale Part Number	Description	Flash / SRAM (Kbytes)	Package	Temperature
MCF51AC256AVFUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 QFP	–40°C to 105°C
MCF51AC256BVFUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 QFP	–40°C to 105°C
MCF51AC256AVLKE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	80 LQFP	–40°C to 105°C
MCF51AC256BVLKE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	80 LQFP	–40°C to 105°C
MCF51AC256AVPUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 LQFP	–40°C to 105°C
MCF51AC256BVPUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 LQFP	–40°C to 105°C
MCF51AC128AVFUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 QFP	–40°C to 105°C
MCF51AC128CVFUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 QFP	–40°C to 105°C
MCF51AC128AVLKE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	80 LQFP	–40°C to 105°C
MCF51AC128CVLKE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	80 LQFP	–40°C to 105°C
MCF51AC128AVPUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 LQFP	–40°C to 105°C
MCF51AC128CVPUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 LQFP	–40°C to 105°C
MCF51AC256ACFUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 QFP	–40°C to 85°C
MCF51AC256BCFUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 QFP	–40°C to 85°C
MCF51AC256ACLKE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	80 LQFP	–40°C to 85°C
MCF51AC256BCLKE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	80 LQFP	–40°C to 85°C

Table 3. Orderable Part Number Summary

MCF51AC256ACPUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCPUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCFGE	MCF51AC256 ColdFire Microcontroller without CAN	256/32	44 LQFP	–40°C to 85°C
MCF51AC128ACFUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 QFP	–40°C to 85°C
MCF51AC128CCFUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 QFP	–40°C to 85°C
MCF51AC128ACLKE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	80 LQFP	–40°C to 85°C
MCF51AC128CCLKE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	80 LQFP	–40°C to 85°CC
MCF51AC128ACPUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 LQFP	–40°C to 85°C
MCF51AC128CCPUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 LQFP	–40°C to 85°C
MCF51AC128CCFGE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	44 LQFP	–40°C to 85°C

1.5 Pinouts and Packaging

Figure 2 shows the pinout of the 80-pin LQFP.

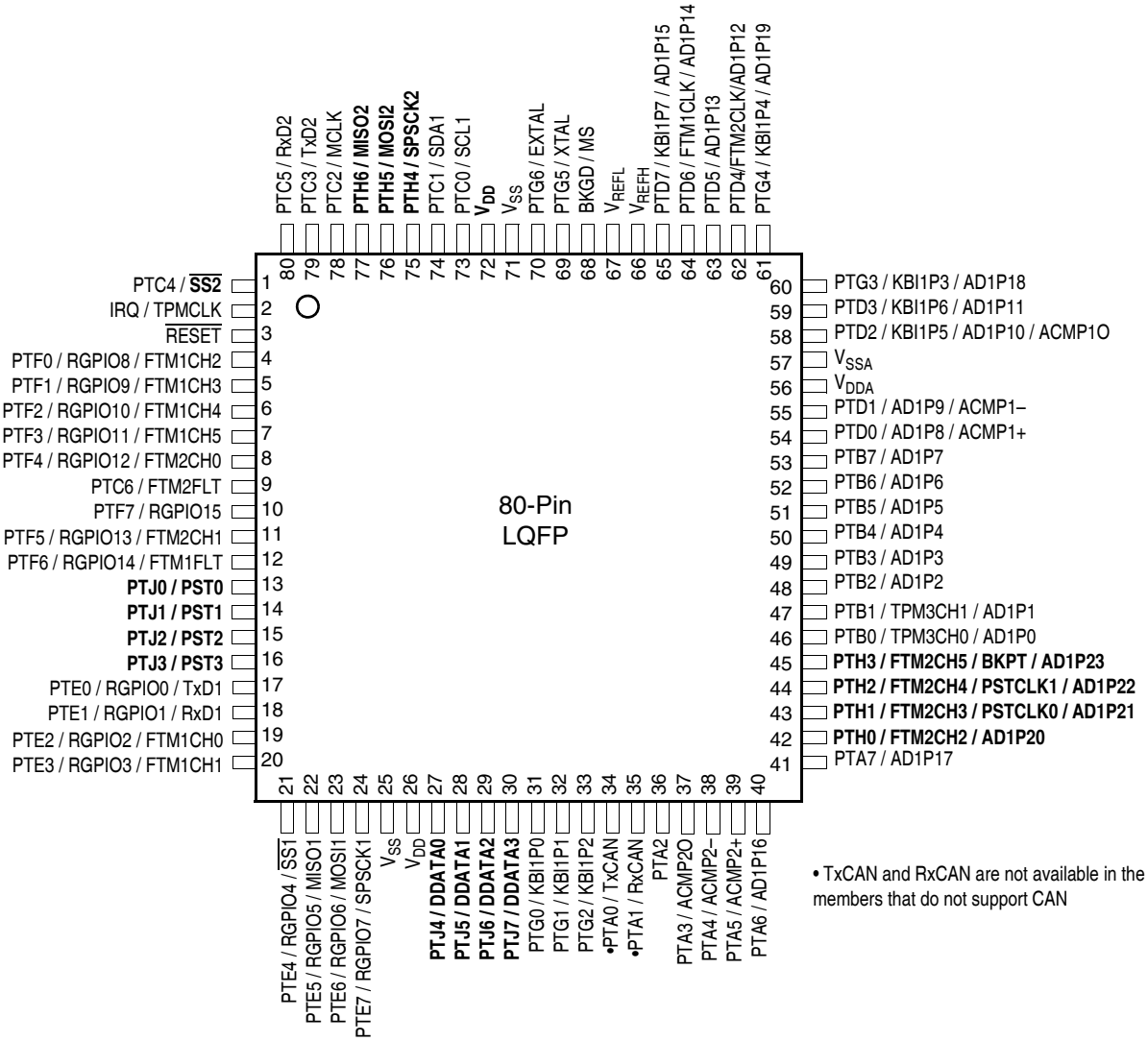


Figure 2. MCF51AC256 Series ColdFire Microcontroller 80-Pin LQFP

Figure 3 shows the pinout of the 64-pin LQFP and QFP.

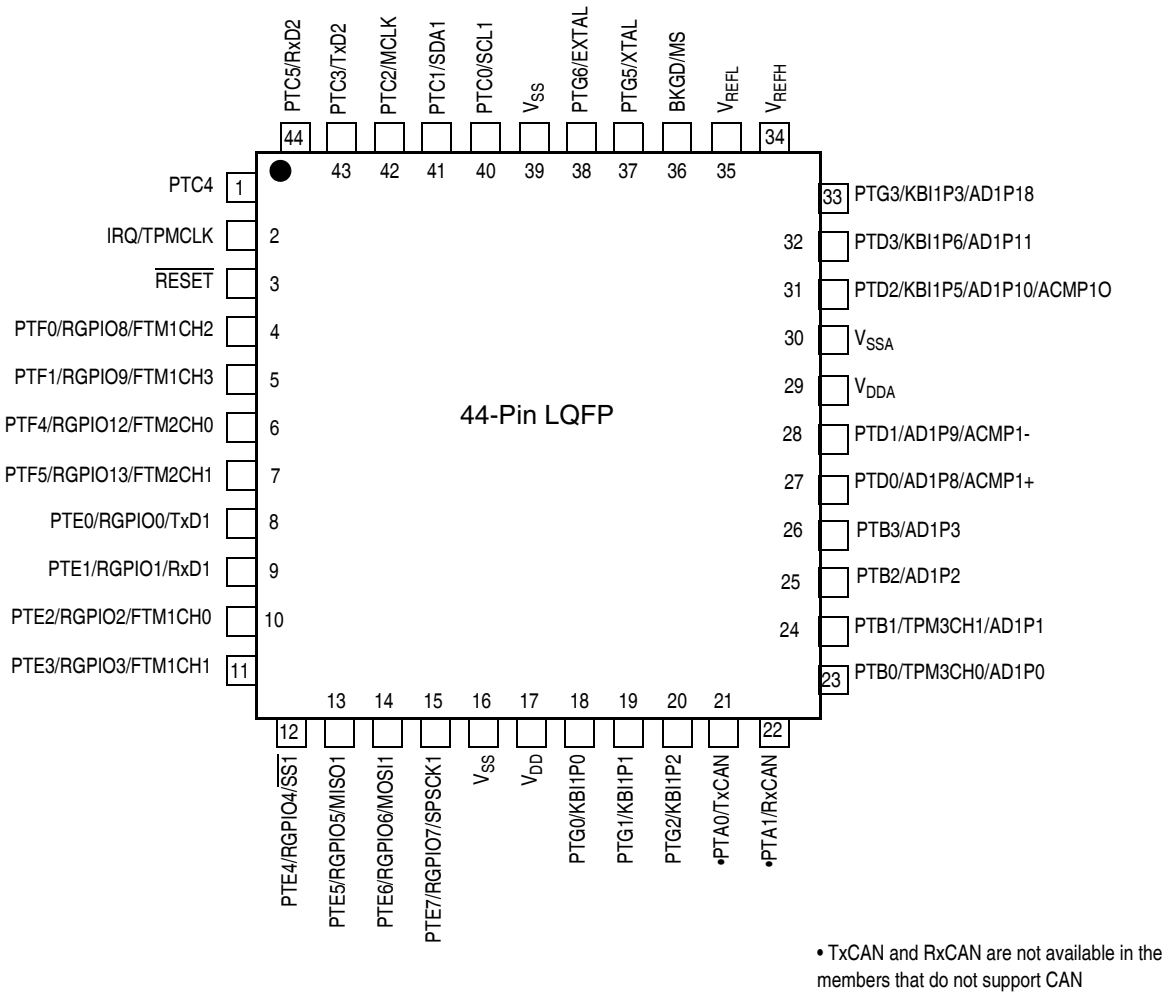


Figure 4. MCF51AC256 Series ColdFire Microcontroller 44-Pin LQFP

Table 4 shows the package pin assignments.

Table 4. Pin Availability by Package Pin-Count

Pin Number			Lowest <-- Priority --> Highest			
80	64	44	Port Pin	Alt 1	Alt 2	Alt 3
1	1	1	PTC4	$\overline{SS2}$		
2	2	2	IRQ	TPMCLK[1]		
3	3	3	$\overline{RESET}$			
4	4	4	PTF0	RGPIO8	FTM1CH2	
5	5	5	PTF1	RGPIO9	FTM1CH3	
6	6	—	PTF2	RGPIO10	FTM1CH4	
7	7	—	PTF3	RGPIO11	FTM1CH5	

Table 6. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to 5.8	V
Input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	±25	mA
Maximum current into V_{DD}	I_{DD}	120	mA
Storage temperature	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low which would reduce overall power consumption.

2.3 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and it is user-determined rather than being controlled by the MCU design. In order to take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 7. Thermal Characteristics

Rating		Symbol	Value	Unit
Operating temperature range (packaged)		T_A	–40 to 105	°C
Maximum junction temperature		T_J	150	°C
Thermal resistance [1,2,3,4]				
80-pin LQFP				
	1s		51	
	2s2p		38	
64-pin LQFP				
	1s		59	
	2s2p	θ_{JA}	41	°C/W
64-pin QFP				
			50	
	1s		36	
	2s2p			
44-pin LQFP				
	1s		67	
	2s2p		45	

1 Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance

2 Junction to Ambient Natural Convection

3 1s — Single layer board, one signal layer

4 2s2p — Four layer board, 2 signal and 2 power layers

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \quad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °C

θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W

$P_D = P_{int} + P_{I/O}$

$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power

$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273°C) \quad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \quad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

2.4 Electrostatic Discharge (ESD) Protection Characteristics

Although damage from static discharge is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with CDF-AEC-Q00 Stress Test Qualification for Automotive Grade Integrated Circuits. (http://www.aecouncil.com/) This device was qualified to AEC-Q100 Rev E.

A device is considered to have failed if, after exposure to ESD pulses, the device no longer meets the device specification requirements. Complete dc parametric and functional testing is performed per the

Table 10. DC Characteristics (continued)

Num	C	Parameter	Symbol	Min	Typical[1]	Max	Unit
22	D	DC injection current[5 6 7 8] (single pin limit) $V_{IN} > V_{DD}$ $V_{IN} < V_{SS}$	I_{IC}	 0 0	—	 2 –0.2	mA
		DC injection current (Total MCU limit, includes sum of all stressed pins) $V_{IN} > V_{DD}$ $V_{IN} < V_{SS}$		 0 0	—	 25 –5	mA

1 Typical values are based on characterization data at 25°C unless otherwise stated.

2 Measured with $V_{In} = V_{DD}$ or V_{SS}.

3 Measured with $V_{In} = V_{SS}$.

4 Measured with $V_{In} = V_{DD}$.

5 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).

6 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

7 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

8 The $\overline{\text{RESET}}$ pin does not have a clamp diode to V_{DD}. Do not drive this pin above V_{DD}.

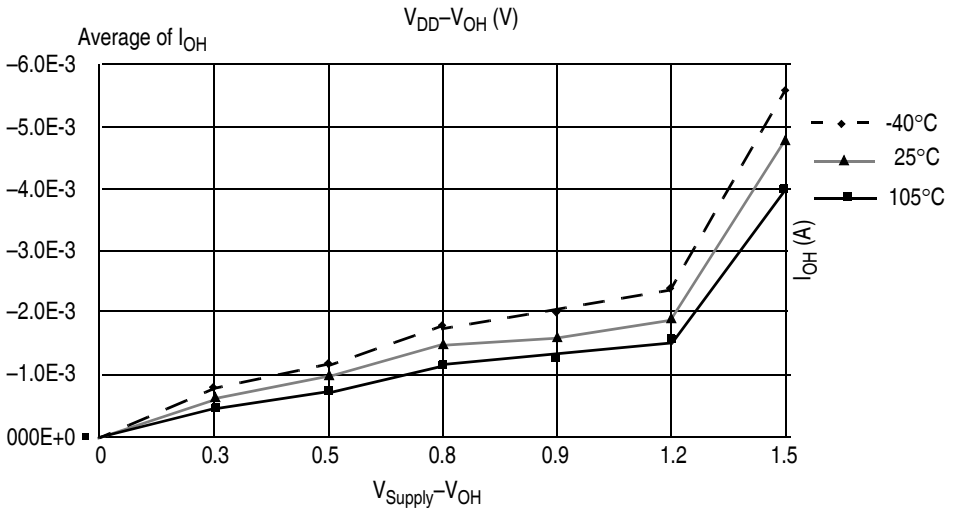


Figure 5. Typical I_{OH} vs. V_{DD}–V_{OH} at V_{DD} = 3 V (Low Drive, PTxDSn = 0)

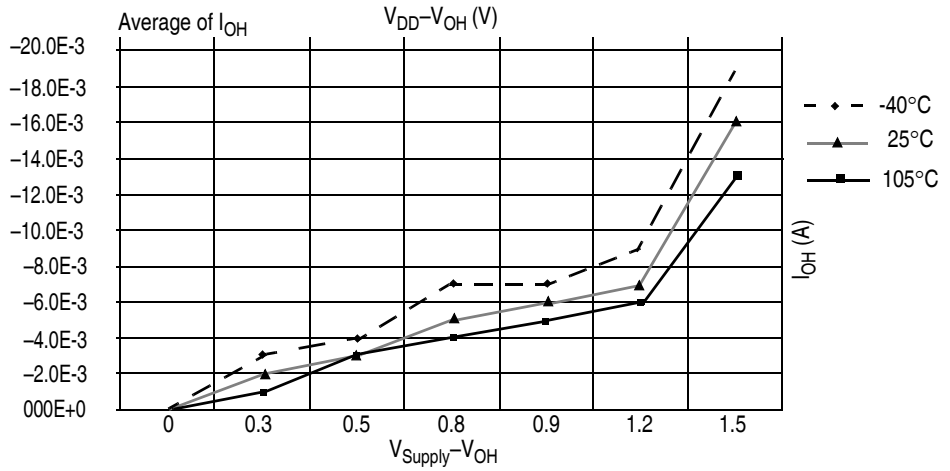


Figure 6. Typical I_{OH} vs. $V_{DD}–V_{OH}$ at V_{DD} = 3 V (High Drive, PTxDSn = 1)

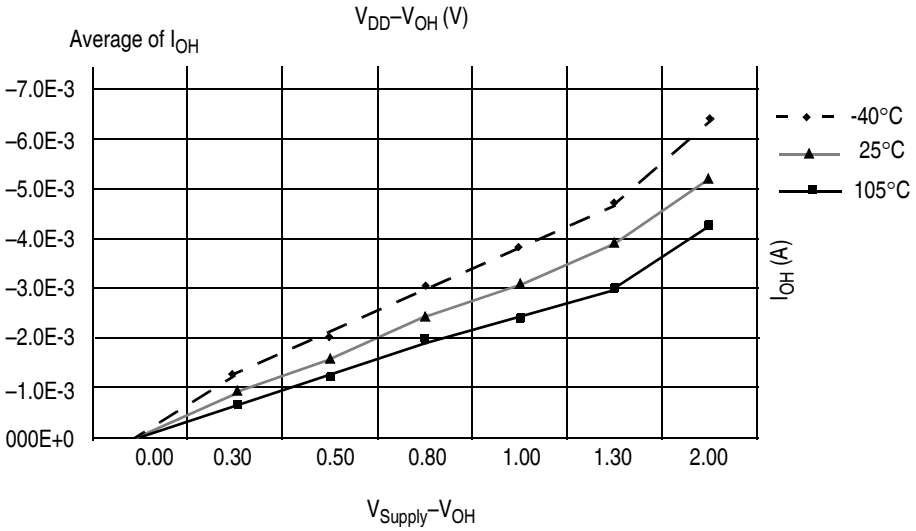


Figure 7. Typical I_{OH} vs. $V_{DD}–V_{OH}$ at V_{DD} = 5 V (Low Drive, PTxDSn = 0)

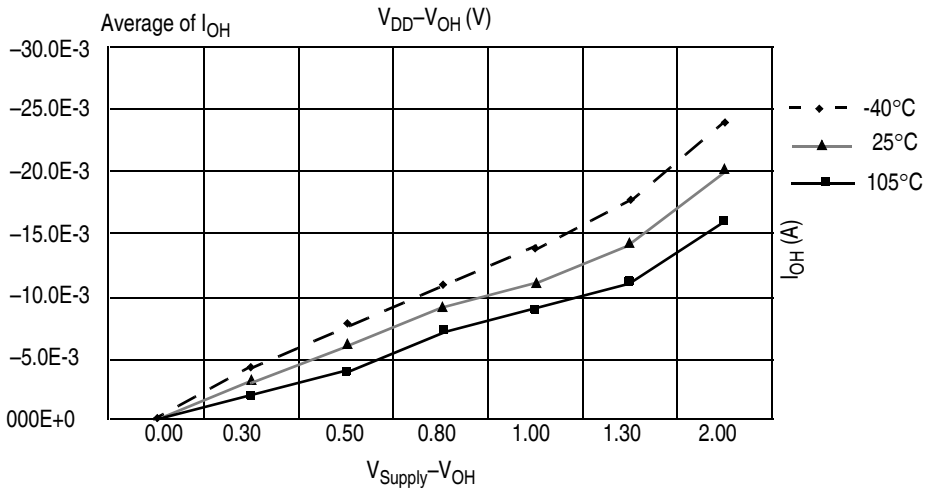


Figure 8. Typical I_{OH} vs. $V_{DD}–V_{OH}$ at V_{DD} = 5 V (High Drive, PTxDSn = 1)

2.6 Supply Current Characteristics

Table 11. Supply Current Characteristics

Num	C	Parameter		Symbol	V_{DD} (V)	Typical[1]	Max[2]	Unit
1	T	Run supply current measured at FEI mode, all modules off, system clock at:	2 MHz	RI_{DD}	5	2.27	—	mA
					3.3	2.24	—	
			4 MHz		5	3.67	—	
					3.3	3.64	—	
			8 MHz		5	6.55	—	
					3.3	6.54	—	
			16 MHz		5	11.90	—	
					3.3	11.85	—	
2	T	Run supply current measured at FEI mode, all modules on, system clock at:	2 MHz		5	3.28	—	
					3.3	3.26	—	
			4 MHz		5	4.33	—	
					3.3	4.32	—	
			8 MHz		5	8.17	—	
					3.3	8.05	—	
			16 MHz		5	14.8	—	
					3.3	14.74	—	
3	T	Run supply current measured at FBE mode, all modules off (RANGE = 1, HGO = 0), system clock at:	2 MHz		5	3.28	—	
					3.3	3.26	—	
			4 MHz		5	4.69	—	
					3.3	4.67	—	
			8 MHz		5	7.48	—	
					3.3	7.46	—	
			16 MHz		5	13.10	—	
					3.3	13.07	—	
4	T	Run supply current measured at FBE mode, all modules on (RANGE = 1, HGO = 0), system clock at:	2 MHz		5	3.64	—	
					3.3	3.63	—	
			4 MHz		5	5.38	—	
					3.3	5.35	—	
			8 MHz		5	8.65	—	
					3.3	8.64	—	
			16 MHz		5	15.55	—	
					3.3	15.40	—	

Table 11. Supply Current Characteristics (continued)

Num	C	Parameter	Symbol	V_{DD} (V)	Typical[1]	Max[2]	Unit
5	C	Wait mode supply[3] current measured at (CPU clock = 2 MHz, f_{Bus} = 1 MHz)	WI_{DD}	5	1.3	2	mA
				3	1.29	2	
6	C	Wait mode supply[3] current measured at (CPU clock = 16 MHz, f_{Bus} = 8 MHz)		5	5.11	8	mA
				3	5.1	8	
7	C	Wait mode supply[3] current measured at (CPU clock = 50 MHz, f_{Bus} = 25 MHz)		5	15.24	25	mA
				3	15.2	25	
8	C	Stop2 mode supply current –40 °C 25 °C 120 °C	$S2I_{DD}$	5	1.40	2.5 2.5 200	µA
		–40 °C 25 °C 120 °C		3	1.16	2.5 2.5 200	µA
9	C	Stop3 mode supply current –40 °C 25 °C 120 °C	$S3I_{DD}$	5	1.60	2.5 2.5 220	µA
		–40 °C 25 °C 120 °C		3	1.35	2.5 2.5 220	µA
10	C	RTI adder to stop2 or stop3[3], 25 °C	$S23I_{DDRTI}$	5	300		nA
				3	300		nA
11	C	Adder to stop3 for oscillator enabled[4] (ERCLKEN =1 and EREFSTEN = 1)	$S3I_{DDOSC}$	5, 3	5		µA

1 Typicals are measured at 25 °C.

2 Values given here are preliminary estimates prior to completing characterization.

3 Most customers are expected to find that auto-wakeup from stop2 or stop3 can be used instead of the higher current wait mode.

4 Values given under the following conditions: low range operation (RANGE = 0), low power mode (HGO = 0).

Figure 9. Typical Run I_{DD} vs. System Clock Freq. for FEI and FBE Modes

2.7 Analog Comparator (ACMP) Electricals

Table 12. Analog Comparator Electrical Specifications

Num	C	Rating	Symbol	Min	Typical	Max	Unit
1	—	Supply voltage	V_{DD}	2.7	—	5.5	V
2	T	Supply current (active)	I_{DDAC}	—	20	35	µA
3	D	Analog input voltage	V_{AIN}	V_{SS} – 0.3	—	V_{DD}	V
4	D	Analog input offset voltage	V_{AIO}	—	20	40	mV
5	D	Analog comparator hysteresis	V_H	3.0	6.0	20.0	mV
6	D	Analog input leakage current	I_{ALKG}	—	—	1.0	µA
7	D	Analog comparator initialization delay	t_{AINIT}	—	—	1.0	µs
8	P	Bandgap voltage reference factory trimmed at V_{DD} = 5.3248 V, Temp = 25 °C	V_{BG}	1.18	1.20	1.21	V

Table 14. 5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) (continued)

Num	C	Characteristic	Conditions	Symb	Min	Typical[1]	Max	Unit	Comment
7	P	Conversion time (including sample time)	Short sample (ADLSMP = 0)	t_{ADC}	—	20	—	ADCK cycles	See Table 10 for conversion time variances
			Long sample (ADLSMP = 1)		—	40	—		
8	T	Sample time	Short sample (ADLSMP = 0)	t_{ADS}	—	3.5	—	ADCK cycles	
			Long sample (ADLSMP = 1)		—	23.5	—		
9	T	Total unadjusted error	12-bit mode	E_{TUE}	—	±3.0	—	LSB[2]	Includes quantization
	P		10-bit mode		—	±1	±2.5		
	T		8-bit mode		—	±0.5	±1.0		
10	T	Differential non-linearity	12-bit mode	DNL	—	±1.75	—	LSB[2]	
	P		10-bit mode[3]		—	±0.5	±1.0		
	T		8-bit mode[3]		—	±0.3	±0.5		
11	T	Integral non-linearity	12-bit mode	INL	—	±1.5	—	LSB[2]	
	T		10-bit mode		—	±0.5	±1.0		
	T		8-bit mode		—	±0.3	±0.5		
12	T	Zero-scale error	12-bit mode	E_{ZS}	—	±1.5	—	LSB[2]	V_{ADIN} = V_{SSA}
	P		10-bit mode		—	±0.5	±1.5		
	T		8-bit mode		—	±0.5	±0.5		
13	T	Full-scale error	12-bit mode	E_{FS}	—	±1	—	LSB[2]	V_{ADIN} = V_{DDA}
	P		10-bit mode		—	±0.5	±1		
	T		8-bit mode		—	±0.5	±0.5		
14	D	Quantization error	12-bit mode	E_Q	—	–1 to 0	—	LSB[2]	
			10-bit mode		—	—	±0.5		
			8-bit mode		—	—	±0.5		
15	D	Input leakage error	12-bit mode	E_{IL}	—	±1	—	LSB[2]	Pad leakage[4] * R_{AS}
			10-bit mode		—	±0.2	±2.5		
			8-bit mode		—	±0.1	±1		
16	D	Temp sensor voltage	25°C	V_{TEMP25}	—	1.396	—	V	
17	D	Temp sensor slope	–40 °C–25 °C	m	—	3.266	—	mV/°C	
			25 °C–85 °C		—	3.638	—		

1 Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 1 LSB = $(V_{REFH} - V_{REFL})/2^N$.

Table 16. MCG Frequency Specifications (continued)(Temperature Range = –40 to 105 °C Ambient)

Num	C	Rating	Symbol	Min	Typical[1]	Max	Unit
18	D	Lock exit frequency tolerance [8]	D_{unl}	±4.47	—	±5.97	%
19	D	Lock time — FLL	t_{fll_lock}	—	—	$t_{fll\_acquire}$+ 1075(1/f_{int_t})	s
20	D	Lock time — PLL	t_{pll_lock}	—	—	$t_{pll\_acquire}$+ 1075(1/f_{pll_ref})	s
21	D	Loss of external clock minimum frequency — RANGE = 0	f_{loc_low}	(3/5) × f_{int}	—	—	kHz

1 Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.

2 The resulting bus clock frequency must not exceed the maximum specified bus clock frequency of the device.

3 This specification applies when the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

4 This specification applies when the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

5 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{BUS}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

6 625 ns represents 5 time quanta for CAN applications, under worst case conditions of 8 MHz CAN bus clock, 1 Mbps CAN bus speed, and 8 time quanta per bit for bit time settings. 5 time quanta is the minimum time between a synchronization edge and the sample point of a bit using 8 time quanta per bit.

7 Below D_{lock} minimum, the MCG enters lock. Above D_{lock} maximum, the MCG will not enter lock. But if the MCG is already in lock, then the MCG may stay in lock.

8 Below D_{unl} minimum, the MCG will not exit lock if already in lock. Above D_{unl} maximum, the MCG is guaranteed to exit lock.

2.11 AC Characteristics

This section describes ac timing characteristics for each peripheral system.

2.11.1 Control Timing

Table 17. Control Timing

Num	C	Parameter	Symbol	Min	Typical[1]	Max	Unit
1	D	Bus frequency (t_{cyc} = 1/f_{Bus})	f_{Bus}	dc	—	24	MHz
2	D	Internal low-power oscillator period	t_{LPO}	800	—	1500	µs
3	D	External reset pulse width[2] (t_{cyc} = 1/f_{Self_reset})	t_{extrst}	100	—	—	ns
4	D	Reset low drive	t_{rstdrv}	66 × t_{cyc}	—	—	ns
5	D	Active background debug mode latch setup time	t_{MSSU}	500	—	—	ns
6	D	Active background debug mode latch hold time	t_{MSH}	100	—	—	ns
7	D	IRQ pulse width Asynchronous path[2] Synchronous path[3]	t_{ILIH}, t_{IHIL}	 100 1.5 × t_{cyc}	—	—	ns
8	D	KBIPx pulse width Asynchronous path[2] Synchronous path[3]	t_{ILIH}, t_{IHIL}	 100 1.5 × t_{cyc}	—	—	ns
9	D	Port rise and fall time (load = 50 pF)[4] Slew rate control disabled (PTxSE = 0), Low Drive Slew rate control enabled (PTxSE = 1), Low Drive Slew rate control disabled (PTxSE = 0), Low Drive Slew rate control enabled (PTxSE = 1), Low Drive	t_{Rise}, t_{Fall}	 — — — —	 11 35 40 75	—	ns

1 Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

2 This is the shortest pulse that is guaranteed to be recognized as a reset pin request. Shorter pulses are not guaranteed to override reset requests from internal sources.

3 This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

4 Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range –40 °C to 105 °C.

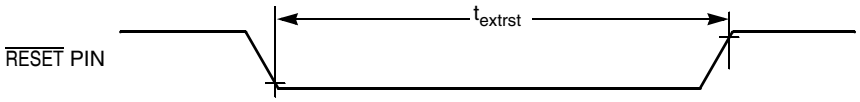


Figure 11. Reset Timing

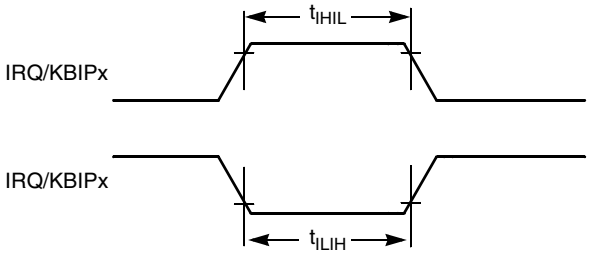
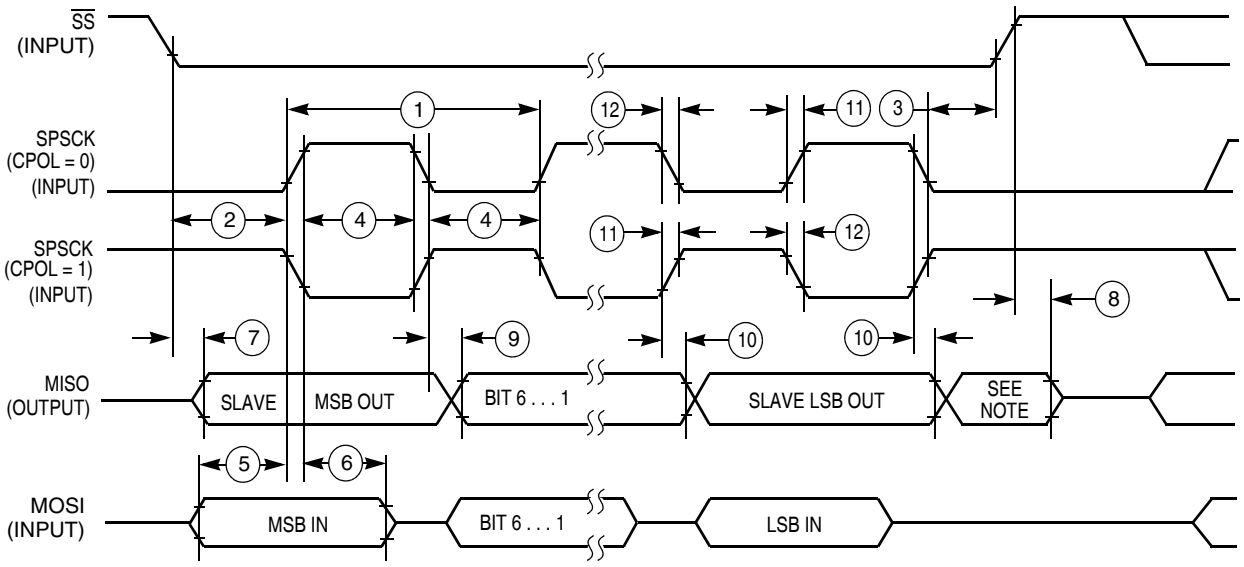


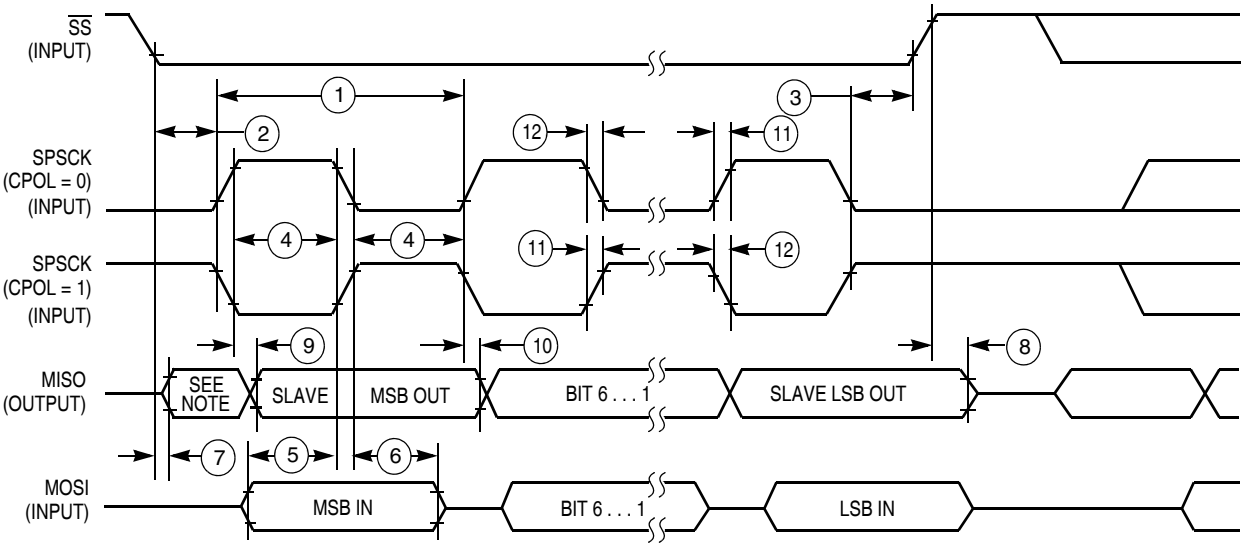
Figure 12. IRQ/KBIPx Timing



NOTE:

1. Not defined but normally MSB of character just received

Figure 17. SPI Slave Timing (CPHA = 0)



NOTE:

1. Not defined but normally LSB of character just received

Figure 18. SPI Slave Timing (CPHA = 1)

2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see Chapter 4, “Memory.”

Table 21. Flash Characteristics

Num	C	Characteristic	Symbol	Min	Typical[1]	Max	Unit
1	—	Supply voltage for program/erase	$V_{prog/erase}$	2.7	—	5.5	V
2	—	Supply voltage for read operation	V_{Read}	2.7	—	5.5	V
3	—	Internal FCLK frequency[2]	f_{FCLK}	150	—	200	kHz
4	—	Internal FCLK period (1/FCLK)	t_{Fcyc}	5	—	6.67	µs
5	—	Byte program time (random location)[2]	t_{prog}	9			t_{Fcyc}
6	—	Byte program time (burst mode)[2]	t_{Burst}	4			t_{Fcyc}
7	—	Page erase time[3]	t_{Page}	4000			t_{Fcyc}
8	—	Mass erase time[2]	t_{Mass}	20,000			t_{Fcyc}
9	C	Program/erase endurance[4] T_L to T_H = –40 °C to 105 °C T = 25 °C	—	10,000 —	— 100,000	— —	cycles
10	C	Data retention[5]	t_{D_ret}	15	100	—	years

1 Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

2 The frequency of this clock is controlled by a software setting.

3 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

4 **Typical endurance for flash** was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, *Typical Endurance for Nonvolatile Memory.*

5 **Typical data retention** values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, *Typical Data Retention for Nonvolatile Memory.*

2.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.14.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East). For more detailed information concerning the evaluation results, conditions and setup, please refer to the EMC Evaluation Report for this device.

3 Mechanical Outline Drawings

Table 22 provides the available package types and their document numbers. The latest package outline/mechanical drawings are available on the MCF51AC256 Series Product Summary pages at http://www.freescale.com.

To view the latest drawing, either:

- Click on the appropriate link in Table 22, or
- Open a browser to the FreescaleÆ website (http://www.freescale.com), and enter the appropriate document number (from Table 22) in the “Enter Keyword” search box at the top of the page.

Table 22. Package Information

Pin Count	Type	Document No.
80	LQFP	98ARL10530D
64	LQFP	98ASS23234W
64	QFP	98ASB42844B
44	LQFP	98ASS23225W

4 Revision History

Table 23. Revision History

Revision	Description
1	Initial published
2	Updated ADC channels, Item 1, 4-5 on Table 2.10
3	Completed all theTBDs. Changed RTC to RTI in Figure 1. Corrected the block diagram. Changed V_{DDAD} to V_{DDA}, V_{SSAD} to V_{SSA}. Added charge device model data and removed machine data in Table 8. Updated the specifications of V_{LVDH}, V_{LVDL}, V_{LVWH} and V_{LVWL} in Table 10. Updated $S2I_{DD}$, $S3I_{DD}$ in Table 11. Added C column in Table 14. Updated f_{dco_DMX32} in Table 16.
4	Corrected the expansion of SPI to serial peripheral interface.
5	Updated V_{LVDL} in the Table 10. Updated RI_{DD} in the Table 11.
6	Updated V_{LVDH}, V_{LVDL}, V_{LVWH} and V_{LVWL} in the Table 10. Added LPO on the Figure 1 and LPO features in the Section 1.3, “Features.”
7	Added 44-pin LQFP package information for AC256 and AC128.